Faquir C Jain

List of Publications by Year
in descending order

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42 papers	255 citations	1163117 8 h-index	996975 15 g-index
42 all docs	42 docs citations	42 times ranked	126 citing authors

#	Article	IF	Citations
1	Quantum-Dot Transistor Based Multi-Bit Multiplier Unit for In-Memory Computing. Selected Topics in Electornics and Systems, 2021, , 53-65.	0.2	0
2	Quantum-Dot Transistor Based Multi-Bit Multiplier Unit for In-Memory Computing. International Journal of High Speed Electronics and Systems, 2020, 29, 2040007.	0.7	0
3	Eightâ€bit ADC using nonâ€volatile flash memory. IET Circuits, Devices and Systems, 2019, 13, 98-102.	1.4	2
4	Fabrication of QDNVMâ€based comparator. Micro and Nano Letters, 2019, 14, 947-951.	1.3	1
5	Highly Linear Amperometric Glucose Detection System Realized in Deep Submicron CMOS Technology. , 2019, , .		1
6	Multi-State 2-Bit CMOS Logic Using n- and p-Quantum Well Channel Spatial Wavefunction Switched (SWS) FETs. Selected Topics in Electornics and Systems, 2019, , 101-112.	0.2	0
7	Multi-State 2-Bit CMOS Logic Using n- and p- Quantum Well Channel Spatial Wavefunction Switched (SWS) FETs. International Journal of High Speed Electronics and Systems, 2018, 27, 1840020.	0.7	2
8	Twin Drain Quantum Well/Quantum Dot Channel Spatial Wave-Function Switched (SWS) FETs for Multi-Valued Logic and Compact DRAMs. International Journal of High Speed Electronics and Systems, 2018, 27, 1840024.	0.7	0
9	Quantum Dot Floating Gate Nonvolatile Random Access Memory Using Ge Quantum Dot Channel for Faster Erasing. International Journal of High Speed Electronics and Systems, 2018, 27, 1840006.	0.7	0
10	Modeling and Fabrication of GeO_x-Ge Cladded Quantum Dot Channel (QDC) FETs on Poly-Silicon. International Journal of High Speed Electronics and Systems, 2018, 27, 1840005.	0.7	0
11	Modeling and Fabrication of GeO_x-Ge Cladded Quantum Dot Channel (QDC) FETs on Poly-Silicon. Selected Topics in Electornics and Systems, 2018, , 43-50.	0.2	0
12	Quantum Dot Floating Gate Nonvolatile Random Access Memory Using Ge Quantum Dot Channel for Faster Erasing. Selected Topics in Electornics and Systems, 2018, , 51-62.	0.2	0
13	Floating Gate Nonvolatile Memory Using Individually Cladded Monodispersed Quantum Dots. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2017, 25, 1774-1781.	3.1	13
14	Multi-Bit NVRAMs Using Quantum Dot Gate Access Channel. International Journal of High Speed Electronics and Systems, 2017, 26, 1740014.	0.7	0
15	Multi-Bit NVRAMs Using Quantum Dot Gate Access Channel. , 2017, , .		0
16	Apparent critical layer thickness in ZnSe/GaAs (001) heterostructures and the role of finite experimental resolution. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 051201.	1.2	2
17	Needle-implantable, wireless biosensor for continuous glucose monitoring. , 2015, , .		5
18	Ternary static random access memory using quantum dot gate fieldâ€effect transistor. Micro and Nano Letters, 2015, 10, 621-624.	1.3	18

#	Article	IF	Citations
19	A Highly Miniaturized Low-Power CMOS-Based pH Monitoring Platform. IEEE Sensors Journal, 2015, 15, 895-901.	4.7	9
20	Design of four-state inverter based on spatial wave-function switched FETs. International Journal of Electronics Letters, 2015, 3, 225-236.	1.2	9
21	Unipolar Logic Gates Based on Spatial Wave-Function Switched FETs. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2015, 23, 609-618.	3.1	11
22	Implementation of Membership Function using Spatial Wave-Function Switched FETs. International Journal of High Speed Electronics and Systems, 2014, 23, 1450007.	0.7	1
23	Implementation of Six Bit ADC and DAC Using Quantum Dot Gate Non-Volatile Memory. Journal of Signal Processing Systems, 2014, 75, 209-216.	2.1	8
24	Low-power signal processing methodologies for implantable biosensing platforms. , 2013, , .		0
25	A low power miniaturized CMOS-based continuous glucose monitoring system. , 2013, , .		1
26	Design of Ternary Logic Combinational Circuits Based on Quantum Dot Gate FETs. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2013, 21, 793-806.	3.1	69
27	Quantum Dot Gate Three-State and Nonvolatile Memory Field-Effect Transistors Using a ZnS/ZnMgS/ZnS Heteroepitaxial Stack as a Tunnel Insulator on Silicon-on-Insulator Substrates. Journal of Electronic Materials, 2013, 42, 3275-3282.	2.2	2
28	ZnS-ZnMgS-ZnS Lattice-Matched Gate Insulator as an Alternative for Silicon Dioxide on Silicon in Quantum Dot Gate FETs (QDGFETs). Journal of Electronic Materials, 2012, 41, 2663-2670.	2.2	13
29	Implementation of unipolar inverter based on spatial wave-function switched FET (SWSFET). , 2012, , .		1
30	Fabrication and Circuit Modeling of NMOS Inverter Based on Quantum Dot Gate Field-Effect Transistors. Journal of Electronic Materials, 2012, 41, 2184-2192.	2.2	19
31	Three-State Quantum Dot Gate FETs Using ZnS-ZnMgS Lattice-Matched Gate Insulator on Silicon. Journal of Electronic Materials, 2011, 40, 1749-1756.	2.2	31
32	Design of ADCs and DACs using 3-state quantum DOT gate FETs. , 2009, , .		6
33	3-State behavior in quantum dot gate FETs. , 2009, , .		1
34	Analysis of Defect Tolerance in Molecular Crossbar Electronics. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2009, 17, 529-540.	3.1	12
35	Multiple Valued Logic Using 3-State Quantum Dot Gate FETs. Multiple-Valued Logic (ISMVL), Proceedings of the International Symposium on, 2008, , .	0.0	6
36	A Quantitative Approach for Analysis of Defect Tolerance in QCA. , 2008, , .		1

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37	Programmable threshold voltage using quantum dot transistors for low-power mobile computing. , 2008, , .		3
38	Design and modeling of a high f<inf>T</inf> and f<inf>max</inf> heterojunction bipolar transistor. , 2007, , .		0
39	Dynamic redundancy allocation for reliable and high-performance nanocomputing. , 2007, , .		3
40	Analysis of defect tolerance in molecular electronics using information-theoretic measures. , 2007, , .		5
41	Pseudo quantum dot behavior due to excitonic transitions in wide gap quantum wire lasers: InGaN-AlGaN and ZnCdSe-ZnMgSSe material systems. , 2007, , .		0
42	Compositional control and structural properties of ZnSe1-xTex epitaxial films on lattice- matched InGaAs/InP (001) by photoassisted Metal Organic Vapor Phase Expitaxy (MOVPE). Materials Research Society Symposia Proceedings, 2004, 819, N3.8.1.	0.1	0